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NEW APPLICATION

LIST OF REFERENCES CITED BY APPLICANT

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
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	AL						
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	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

VIN	AW	Roy SCHEUERLEIN, et al., "A10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell" IEEE International Solid State Circuits Conference(ISSCC) Digest of Technical Papers, pp. 128-129, February 8, 2000
VIN	AX	M. Durlam, et al., "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", IEEE International Solid-State Circuits Conference, (ISSCC) Digest of Technical Papers, pp. 130-131, February 8, 2000
VIN	AY	Peter K. Naji, et al., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM", IEEE International Solid-State Circuits Conference (ISSCC) Digest of Technical Papers, pp. 122-123, February 6, 2001
	AZ	

☐ Additional References sheet(s) attached

Examiner

W. Huel

Date Considered

9/7/04

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.